

10-25-00
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534 Rec'd PCT/PTC 26 JUL 2000

194310US2 PCT

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF:

LÉA DI CIOCCIO

: ATTN: APPLICATION DIVISION

SERIAL NO: NEW U.S. PCT APPLICATION
(Based on PCT/FR99/00155)

FILED: HERewith

: EXAMINER:

FOR: PROCESS FOR FABRICATING
A STRUCTURE OF SEMICONDUCTOR-
ON-INSULATOR TYPE, IN PARTICULAR
SICOI

PRELIMINARY AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Prior to a first examination on the merits, please amend the above-identified
application as follows:

IN THE SPECIFICATION

Page 1, before line 1, insert:

--TITLE OF THE INVENTION--;

actual line 3, delete in its entirety and substitute therefor:

--BACKGROUND OF THE INVENTION

Field of the Invention--;

prenumbered line 25, delete in its entirety and substitute therefor:

--Discussion of the Background--.

Page 4, prenumbered line 29, delete in its entirety and substitute therefor:

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